

# **Product Description**

The PE4134 is a high linearity, passive Quad MOSFET Mixer for PCS & 3G Base Station Receivers, exhibiting high dynamic range performance over a broad LO drive range of up to +20 dBm. This mixer integrates passive matching networks to provide single-ended interfaces for the RF and LO ports, eliminating the need for external RF baluns or matching networks. The PE4134 is optimized for frequency down-conversion using low-side LO injection for PCS & 3G Base Station applications, and is also suitable for up-conversion applications.

The PE4134 is manufactured in Peregrine's patented Ultra-Thin Silicon (UTSi®) CMOS process, offering the performance of GaAs with the economy and integration of conventional CMOS.

### Figure 1. Functional Schematic Diagram



### Table 1. Electrical Specifications @ +25 °C

# PE4134

# High Linearity Quad MOSFET Mixer for PCS & 3G BTS

### Features

- Integrated, single-ended RF & LO interfaces
- High linearity: IIP3 >+31 dBm, 1.9 GHz (+17 dBm LO)
- Low-conversion loss: 7.4 dB (+17 dBm LO)
- High isolation: Typical LO-IF at 33 dB, LO-RF at 31 dB
- Optimized for low-side LO injection
- Packaged in a 6-lead 3x3mm MLPM

### Figure 2. Package Type

		6
2	6-lead MLPM 3 x 3 mm	5
		4

Parameter	Minimum	Typical	Maximum	Units
Frequency Range:				
LO	1540		1740	MHz
RF	1800		2000	MHz
IF*		260		MHz
Conversion Loss**		7.4	8.0	dB
Isolation:				
LO-RF	27	31		dB
LO-IF	27	33		dB
Input IP3				
1.8GHz	26	29		dBm
1.9GHz	31	33		dBm
2.0GHz	28	31		dBm
Input 1 dB Compression		22		dBm

\*An IF frequency of 260 MHz is a nominal frequency. The IF frequency can be specified by the user as long as the RF and LO frequencies are within the specified maximum and minimum.

\*\*Conversion Loss includes loss of IF transformer (M/A COM ETK4-2T, nominal loss 0.7 dB at 260 MHz).

Test conditions unless otherwise noted: IF = 260 MHz, LO input drive = 17 dBm, RF input drive = 3 dBm.

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# Figure 3. Pin Configuration



# **Table 2. Pin Descriptions**

Pin No.	Pin Name	Description
1	IF1	IF differential output
2	GND	Ground connections for Mixer. Traces should be physically short and connect immediately to ground plane for best performance. The exposed solder pad must also be soldered to the ground plane for best performance.
3	LO	LO Input
4	RF	RF Input
5	GND	Ground connections for Mixer. Traces should be physically short and connect immediately to ground plane for best performance. The exposed solder pad must also be soldered to the ground plane for best performance.
6	IF2	IF differential output

### **Table 3. Absolute Maximum Ratings**

Symbol	Parameter/Conditions	Min	Max	Units
T <sub>ST</sub>	Storage temperature range	-65	150	°C
T <sub>OP</sub>	Operating temperature range	-40	85	°C
P <sub>LO</sub>	LO input power		20	dBm
P <sub>RF</sub>	RF input power		12	dBm
$V_{ESD}$	ESD Sensitive Device		250	V

# **Electrostatic Discharge (ESD) Precautions**

When handling this UTSi device, observe the same precautions that you would use with other ESDsensitive devices. Although this device contains circuitry to protect it from damage due to ESD, precautions should be taken to avoid exceeding the rating specified.

### Latch-Up Avoidance

Unlike conventional CMOS devices, UTSi CMOS devices are immune to latch-up.



### Figure 4. Evaluation Board Schematic Diagram



T2, M/A-Com E-Series RF 4:1 Transformer, 2.0 – 1000 MHz, ETK4-2T





### Table 4. Bill of Materials

Reference	Value / Description
T2	M/A Com ETK4-2T
R1	0Ω
U1	PE4134 MLP Mixer
J1, J2, J3	SMA Connector

Figure 6. Evaluation Board Testing Block Diagram, 2-Tone Setup



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Figure 9. Input IP3

IIP3 (dBm)

# Typical Performance Data (LO=17 dBm, RF=3 dBm, IF=260 MHz)

# Figure 7. Conversion Loss



85°C 25°C -40°C 1dB Compression (dB) Frequency (MHz)

# Figure 8. Input 1dB Compression

Figure 10. Output IP3



85°C 25°C -40°C OIP3 (dBm) Frequency (MHz)



# Typical Performance Data (LO=17 dBm, RF=3 dBm, IF=260 MHz)





Figure 12. LO-RF Isolation vs. Frequency



Figure 13. LO Port Return Loss @ 25°C



Figure 14. RF Port Return Loss @ 25°C





# Typical Performance Data @ +25 °C (RF=3 dBm, IF=260 MHz)



# Figure 15. Conversion Loss across LO Power



#### Figure 16. Input IP3 across LO Power

### Table 5. Spurious Response

Spurious Response						
	mRF+nLO					
	nLO					
mRF	1 2 3 4					
1	5	37	30	50		
2	49 55 65 59					
3	75	>85	78	80		
4	>85 84 >85 >85					

Normalized to dB below PIF

(RF=1900Mhz @ 3dBm, LO=1640MHz @ 17dBm)

### Table 6. Spurious Response

Spurious Response						
	mRF+nLO					
	nLO					
mRF	1 2 3 4					
1	0	32	22	43		
2	57	49	61	62		
3	64	71	64	65		
4	>85	>85	>85	81		

Normalized to dB below PIF

(RF=1900Mhz @ 3dBm, LO=1640MHz @ 17dBm)



# Figure 17. Package Drawing

6-lead MLPM



3 COPLANARITY APPLIES TO EXPOSED HEAT SLUG AS WELL AS THE TERMINALS.

A PROFILE TOLERANCE APPLIES TO PLASTIC BODY ONLY.

# Table 7. Ordering Information

Order Code	Part Marking	Description	Package	Shipping Method
4134-01	4134	PE4134-06MLP3x3-12800F	6-lead 3x3 MLPM	12800 units / Canister
4134-02	4134	PE4134-06MLP3x3-3000C	6-lead 3x3 MLPM	3000 units / T&R
4134-00	4134-EK	PE4134-06MLP3x3-EK	Evaluation Board	1 / Box



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The product is in a formative or design stage. The data sheet contains design target specifications for product development. Specifications and features may change in any manner without notice.

### **Preliminary Specification**

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